

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	965	wafer and thin\$6 and polish\$4 and remov\$4 with oxide and ((oxide with free) or (oxygen adj free) or (precipitate with free))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/22 18:18
L2	960	wafer and thin\$6 and polish\$4 and remov\$4 with oxide and ((oxide with free) or (oxygen adj free) or (precipitate with free) with (wafer or substrate))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/22 18:19
L3	732	wafer and (thin\$6 with (wafer or substrate)) and polish\$4 and remov\$4 with oxide and ((oxide with free) or (oxygen adj free) or (precipitate with free) with (wafer or substrate))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/22 18:26
L4	731	wafer and (thin\$6 with (wafer or substrate)) and polish\$4 and remov\$4 with oxide and ((oxide with free) or (oxygen adj free) or (precipitate with free) with (wafer or substrate) and micrometer)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/22 18:20
L5	731	wafer and (thin\$6 with (wafer or substrate)) and polish\$4 and remov\$4 with oxide and ((oxide with free) or (oxygen adj free) or (precipitate with free) with (wafer or substrate) with micrometer)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/22 18:22
L6	2	((thinning with wafer) or (thinned with wafer)) and ((oxygen or oxide or precipitate) with free with (zone or region or area)) and (oxide with growth with ("nm" or nanometers)) and (polish\$4 with thinned with wafer)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/22 18:26
L7	4095	438/692	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/22 18:26
L8	42	7 and wafer and (thin\$6 with (wafer or substrate)) and polish\$4 and remov\$4 with oxide and ((oxide with free) or (oxygen adj free) or (precipitate with free) with (wafer or substrate))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/22 18:26

L9	2286	438/692.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/22 18:29
L10	32	9 and wafer and (thin\$6 with (wafer or substrate)) and polish\$4 and remov\$4 with oxide and ((oxide with free) or (oxygen adj free) or (precipitate with free) with (wafer or substrate))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/22 18:29
L11	16	("5855735" "5919302" "6236104"  "6284039" "6342725" "6384415"  "6387466" "6416836" "6565649" ).PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/22 18:29
L12	799	438/691.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/22 18:29
L13	6	12 and wafer and (thin\$6 with (wafer or substrate)) and polish\$4 and remov\$4 with oxide and ((oxide with free) or (oxygen adj free) or (precipitate with free) with (wafer or substrate))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/22 18:31
L14	832	438/459.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/22 18:33
L15	6	13 and wafer and (thin\$6 with (wafer or substrate)) and polish\$4 and remov\$4 with oxide and ((oxide with free) or (oxygen adj free) or (precipitate with free) with (wafer or substrate))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/22 18:32
L16	400	117/3.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/22 18:31

L17	5	16 and wafer and (thin\$6 with (wafer or substrate)) and polish\$4 and remov\$4 with oxide and ((oxide with free) or (oxygen adj free) or (precipitate with free) with (wafer or substrate))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/22 18:33
L18	3848	438/694.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/22 18:33
L19	651	438/705.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/22 18:33
L20	5	18 and wafer and (thin\$6 with (wafer or substrate)) and polish\$4 and remov\$4 with oxide and ((oxide with free) or (oxygen adj free) or (precipitate with free) with (wafer or substrate))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/22 18:34
L21	9	19 and wafer and (thin\$6 with (wafer or substrate)) and polish\$4 and remov\$4 with oxide and ((oxide with free) or (oxygen adj free) or (precipitate with free) with (wafer or substrate))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/22 18:34